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APPLICATION NO.	FII	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/013,103	,103 11/06/2001		Krishna Seshan	42390P5778D	1577
8791	7590 08/24/2005			EXAMINER	
		OFF TAYLOR &	LEWIS, MONICA		
12400 WILSHIRE BOULEVARD SEVENTH FLOOR				ART UNIT	PAPER NUMBER
LOS ANGELES, CA 90025-1030			2822		
				DATE MAILED: 08/24/2005	5

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)						
	10/013,103	SESHAN ET AL.	ı					
Office Action Summary	Examiner	Art Unit						
	Monica Lewis	2822						
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	orrespondence address						
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period of Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time y within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE.	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).						
Status								
1) Responsive to communication(s) filed on 11 Ju	<i>aly</i> 2005.							
,	action is non-final.							
·— · · ·	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposition of Claims								
4) Claim(s) 17-29 is/are pending in the application 4a) Of the above claim(s) 23-26 is/are withdray 5) Claim(s) is/are allowed. 6) Claim(s) 17-22 and 27-29 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/o	vn from consideration.							
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 12 September 2002 is/a Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Ex	are: a) $\boxtimes$ accepted or b) $\square$ objec drawing(s) be held in abeyance. See tion is required if the drawing(s) is obj	e 37 CFR 1.85(a). lected to. See 37 CFR 1.121(d).						
,								
Priority under 35 U.S.C. § 119  12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage						
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:							

Art Unit: 2822

## **DETAILED ACTION**

This action is in response to the request for election filed July 11, 2005. 1.

## Specification

The lengthy specification has not been checked to the extent necessary to determine the 2. presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

## Continued Examination Under 37 CFR 1.114

3. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 3/25/05 has been entered.

## Election/Restrictions

Applicant's election of Embodiment I in the reply filed on 7/11/05 is acknowledged. 4. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Application/Control Number: 10/013,103 Page 3

Art Unit: 2822

## Claim Rejections - 35 USC § 103

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claim 27 is rejected under 35 U.S.C. 102(e) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Cox (U.S. Patent No. 6,166,439).

In regards to claim 27, Cox discloses the following:

- a) a substrate (50b) (For Example: See Figure 4H);
- b) an insulating layer (50a) formed directly on the substrate (For Example: See Figure 4H);
- c) at least one conductive structure (54) formed directly on the insulating layer (For Example: See Figure 4H);
  - d) a first layer (61) (For Example: See Figure 4H);
- e) the first layer is disposed between the insulating layer and the second layer (59) (For Example: See Figure 4H);
- f) the first layer and the second layer comprise one common chemical element other than silicon (For Example: See Column 7 Lines 44-46 and Column 8 Lines 12-16); and
- g) the second layer is a passivation layer formed on the first layer (For Example: See Figure 4H).

Finally, the following limitation makes it a product by process claim: a) "formed from a modification of a portion of the insulating layer." The MPEP § 2113, states, "Even though product -by[-] process claims are limited by and defined by the process, determination of patentability is based upon the product itself. The patentability of a product does not depend on its method of production. If the product in product-by-process claim is the same as or obvious

Application/Control Number: 10/013,103 Page 4

Art Unit: 2822

from a product of the prior art, the claim is unpatentable even though the prior product is made by a different process." *In re Thorpe*, 227 USPQ 964, 966 (Fed. Cir. 1985)(citations omitted).

A "product by process" claim is directed to the product per se, no matter how actually made, In re Hirao and Sato et al., 190 USPQ 15 at 17 (CCPA 1976) (footnote 3). See also In re Brown and Saffer, 173 USPQ 685 (CCPA 1972): In re Luck and Gainer, 177 USPQ 523 (CCPA 1973); In re Fessmann, 180 USPQ 324 (CCPA 1974); and In re Marosi et al., 218 USPQ 289 (CAFC 1983) final product per se which must be determined in a "product by, all of" claim, and not the patentability of the process, and that an old or obvious product, whether claimed in "product by process" claims or not. Note that Applicant has the burden of proof in such cases, as the above caselaw makes clear.

7. Claims 17-19, 21, 22 and 29 are rejected under 35 U.S.C. 103(a) as obvious over Cox (U.S. Patent No. 6,166,439) in view of Applicant's Prior Art.

In regards to claim 17, Cox discloses the following:

- a) a substrate (50b) comprising at least one level of interconnection (For Example: See Figure 4H);
- b) an insulating layer (50a) formed directly on a surface of the substrate (For Example: See Figure 4H);
- c) at least one conductive structure (54) formed directly on the insulating layer, the conductive structure comprising a contact to the at least one level of interconnection of the substrate (For Example: See Figure 4H);
- d) an adhesion layer (61) formed on a top surface of said insulating layer (For Example: See Figure 4H); and
- e) a first passivation layer (59) formed on a top surface of said adhesion layer (For Example: See Figure 4H).

Application/Control Number: 10/013,103

Art Unit: 2822

In regards to claim 17, Cox fails to disclose the following:

a) a first passivation layer formed on a top surface of the conductive structure.

However, Applicant's Prior Art discloses a semiconductor device that has a first passivation layer (40) formed on a top surface of the conductive structure (33) (For Example: See Figure 6). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a first passivation layer formed on a top surface of the conductive structure as disclosed in Applicant's Prior Art because it aids in protecting the device from scratches, moisture and impurities (For Example: See Page 10 Lines 9 and 10).

Additionally, since Cox and Applicant's Prior Art are both from the same field of endeavor, the purpose disclosed by Applicant's Prior Art would have been recognized in the pertinent art of Cox.

In regards to claim 18, Cox fails to disclose the following:

a) a second passivation layer formed upon said first passivation layer.

However, Applicant's Prior Art discloses a semiconductor device that has a second passivation layer (45) formed upon said first passivation layer (40) (For Example: See Figure 6). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a second passivation layer formed upon said first passivation layer as disclosed in Applicant's Prior Art because it aids in protecting the device from scratches, moisture and impurities (For Example: See Page 10 Lines 9 and 10).

Application/Control Number: 10/013,103

Art Unit: 2822

Additionally, since Cox and Applicant's Prior Art are both from the same field of endeavor, the purpose disclosed by Applicant's Prior Art would have been recognized in the pertinent art of Cox.

In regards to claim 19, Cox discloses the following:

a) oxide layer includes silicon dioxide ( $Si0_2$ ) (For Example: See Page 5 Lines 1-7).

In regards to claim 21, Cox fails to disclose the following:

a) first passivation layer includes silicon nitride (Si<sub>3</sub>N<sub>4</sub>).

However, Applicant's Prior Art discloses a semiconductor device that has a first passivation layer (40) that includes silicon nitride (Si<sub>3</sub>N<sub>4</sub>) (For Example: See Figure 6 and Page 10 Line 15). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a semiconductor device that has a first passivation layer that includes silicon nitride as disclosed in Applicant's Prior Art because it aids in protecting the device from scratches, moisture and impurities (For Example: See Page 10 Lines 9 and 10).

Additionally, since Cox and Applicant's Prior Art are both from the same field of endeavor, the purpose disclosed by Applicant's Prior Art would have been recognized in the pertinent art of Cox.

In regards to claim 22, Cox fails to disclose the following:

a) second passivation layer includes polyimide.

However, Applicant's Prior Art discloses a semiconductor device that has a second passivation layer (45) that includes polyimide (For Example: See Figure 6 and

Art Unit: 2822

Page 10 Line 16). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a semiconductor device that has a second passivation layer that includes polyimide as disclosed in Applicant's Prior Art because it aids in protecting the device from scratches, moisture and impurities (For Example: See Page 10 Lines 9 and 10).

Additionally, since Cox and Applicant's Prior Art are both from the same field of endeavor, the purpose disclosed by Applicant's Prior Art would have been recognized in the pertinent art of Cox.

In regards to claim 29, Cox fails to disclose the following:

a) second layer includes silicon nitride (Si<sub>3</sub>N<sub>4</sub>).

However, Applicant's Prior Art discloses a semiconductor device that has a second layer (40) that includes silicon nitride (Si<sub>3</sub>N<sub>4</sub>) (For Example: See Figure 6 and Page 10 Line 15). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a semiconductor device that has a second layer that includes silicon nitride as disclosed in Applicant's Prior Art because it aids in protecting the device from scratches, moisture and impurities (For Example: See Page 10 Lines 9 and 10).

Additionally, since Cox and Applicant's Prior Art are both from the same field of endeavor, the purpose disclosed by Applicant's Prior Art would have been recognized in the pertinent art of Cox.

Application/Control Number: 10/013,103

Art Unit: 2822

8. Claim 20 is rejected under 35 U.S.C. 103(a) as obvious over Cox (U.S. Patent

No. 6,166,439) in view of Applicant's Prior Art and Dass et al. (U.S. Patent No. 6,046,101).

In regards to claim 20, Cox fails to disclose the following:

a) adhesion layer includes silicon oxynitride.

However, Dass et al. ("Dass") discloses a semiconductor device that has an adhesion layer that includes silicon oxynitride (For Example: See Column 7 Line 19). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a semiconductor device that has an adhesion layer that includes silicon oxynitride as disclosed in Dass because it aids in protecting the conductive structure from contamination (For Example: See Page 7 Lines 59-63).

Additionally, since Cox and Dass are both from the same field of endeavor, the purpose disclosed by Dass would have been recognized in the pertinent art of Cox.

9. Claim 28 is rejected under 35 U.S.C. 103(a) as obvious over Cox (U.S. Patent No. 6,166,439) in view of Dass et al. (U.S. Patent No. 6,046,101).

In regards to claim 28, Cox fails to disclose the following:

a) the first layer includes silicon oxynitride.

However, Dass discloses a semiconductor device that has a first layer that includes silicon oxynitride (For Example: See Column 7 Line 19). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor of Cox to include a semiconductor device that has a first layer that includes silicon oxynitride as disclosed in Dass because it aids in protecting the conductive structure from contamination (For Example: See Page 7 Lines 59-63).

Application/Control Number: 10/013,103 Page 9

Art Unit: 2822

Additionally, since Cox and Dass are both from the same field of endeavor, the purpose disclosed by Dass would have been recognized in the pertinent art of Cox.

#### Conclusion

10. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica Lewis whose telephone number is 571-272-1838.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300 for regular and after final communications. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

ML August 18, 2005

> MLQ 2822